

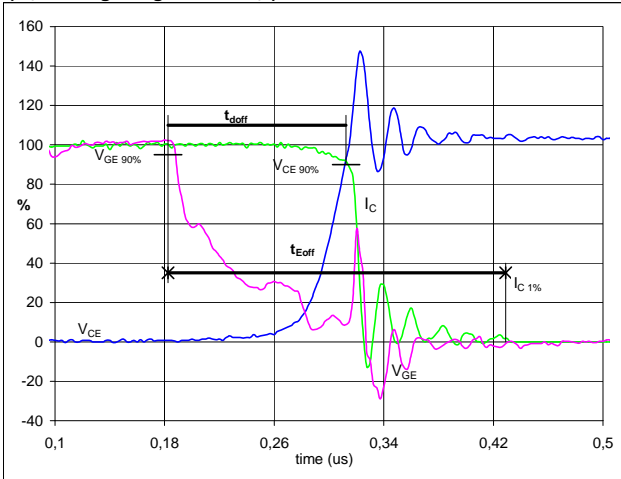
Switching Definitions INPUT BOOST MOSFET+IGBT

General conditions	
T_j	= 125 °C
$R_{gon\ IGBT}$	= 4 Ω
$R_{goff\ IGBT}$	= 4 Ω

MOSFET turn off delayed by 100ns

Figure 1 INPUT BOOST MOSFET+IGBT

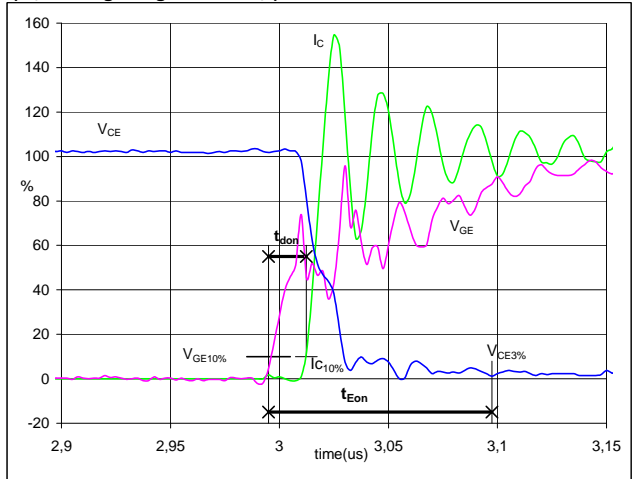
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



$V_{GE} (0\%) =$	0	V
$V_{GE} (100\%) =$	15	V
$V_C (100\%) =$	350	V
$I_C (100\%) =$	77	A
$t_{doff} =$	0,12	μs
$t_{Eoff} =$	0,25	μs

Figure 2 INPUT BOOST MOSFET+IGBT

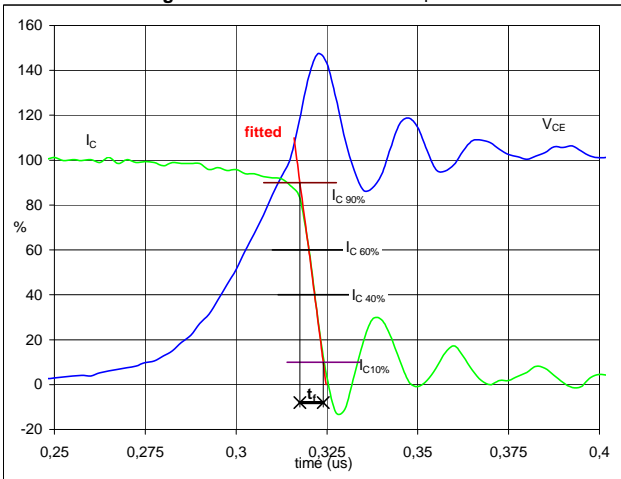
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon}
(t_{Eon} = integrating time for E_{on})



$V_{GE} (0\%) =$	0	V
$V_{GE} (100\%) =$	15	V
$V_C (100\%) =$	350	V
$I_C (100\%) =$	77	A
$t_{don} =$	0,02	μs
$t_{Eon} =$	0,10	μs

Figure 3 INPUT BOOST MOSFET+IGBT

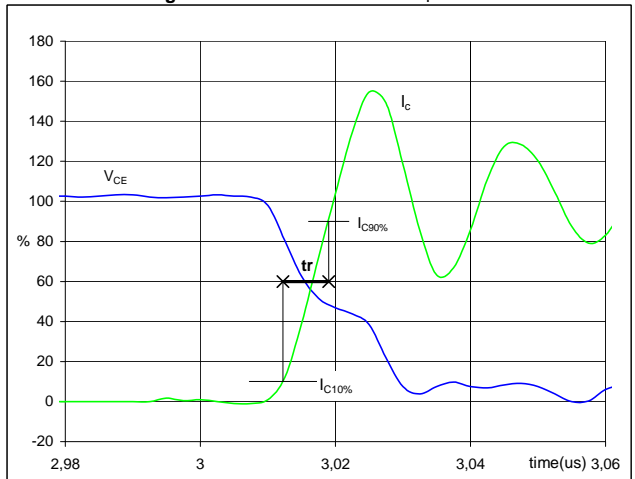
Turn-off Switching Waveforms & definition of t_f



$V_C (100\%) =$	350	V
$I_C (100\%) =$	77	A
$t_f =$	0,007	μs

Figure 4 INPUT BOOST MOSFET+IGBT

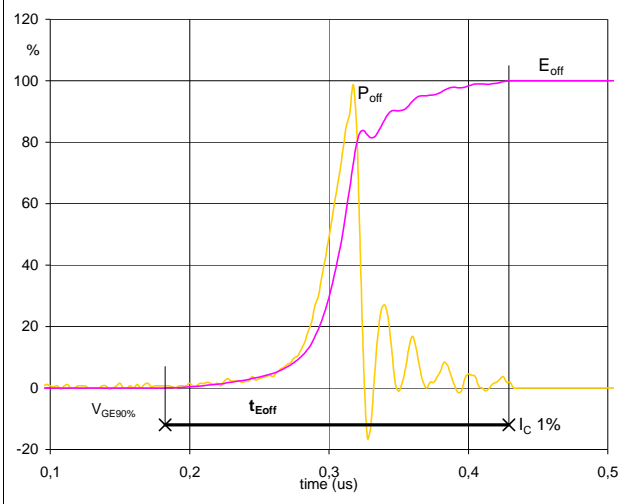
Turn-on Switching Waveforms & definition of t_r



$V_C (100\%) =$	350	V
$I_C (100\%) =$	77	A
$t_r =$	0,007	μs

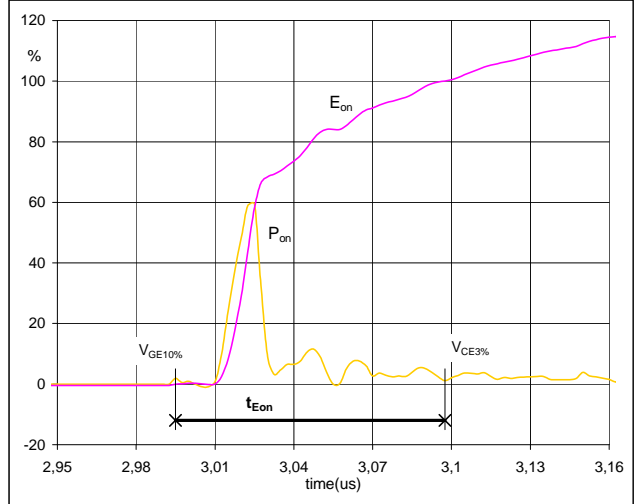
Switching Definitions INPUT BOOST MOSFET+IGBT

Figure 5 INPUT BOOST MOSFET+IGBT

Turn-off Switching Waveforms & definition of t_{Eoff}


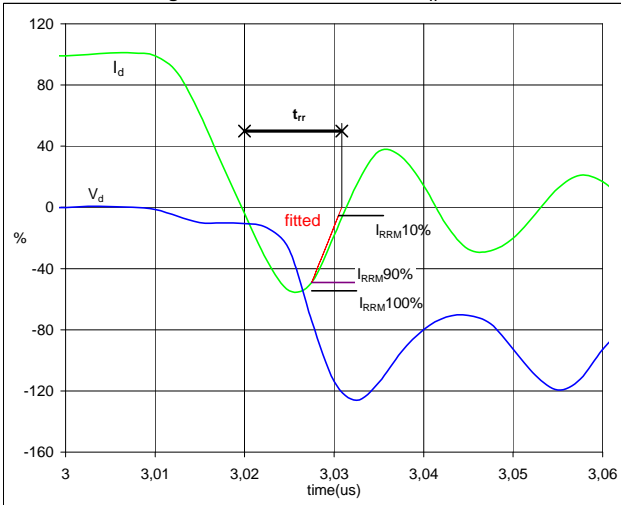
$P_{off}(100\%) =$	27,11	kW
$E_{off}(100\%) =$	0,84	mJ
$t_{Eoff} =$	0,25	μs

Figure 6 INPUT BOOST MOSFET+IGBT

Turn-on Switching Waveforms & definition of t_{Eon}


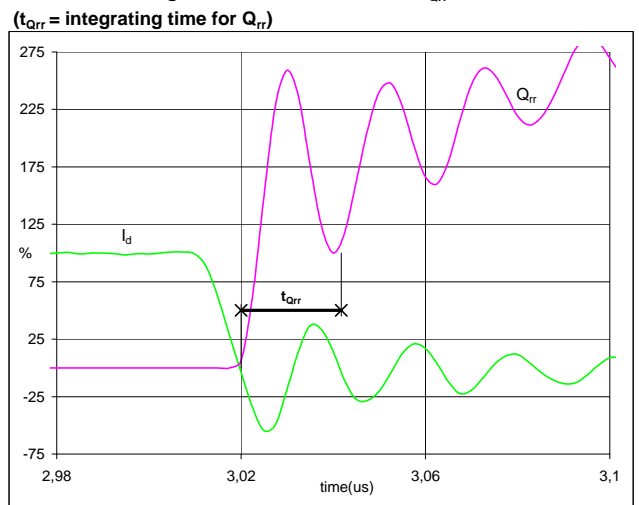
$P_{on}(100\%) =$	27,11	kW
$E_{on}(100\%) =$	0,29	mJ
$t_{Eon} =$	0,10	μs

Figure 7 INPUT BOOST MOSFET+IGBT

Turn-off Switching Waveforms & definition of t_{rr}


$V_d(100\%) =$	350	V
$I_d(100\%) =$	77	A
$I_{RRM}(100\%) =$	-43	A
$t_{rr} =$	0,012	μs

Figure 8 INPUT BOOST MOSFET+IGBT

Turn-on Switching Waveforms & definition of t_{Qrr}


$I_d(100\%) =$	77	A
$Q_{rr}(100\%) =$	0,60	μC
$t_{Qrr} =$	0,02	μs

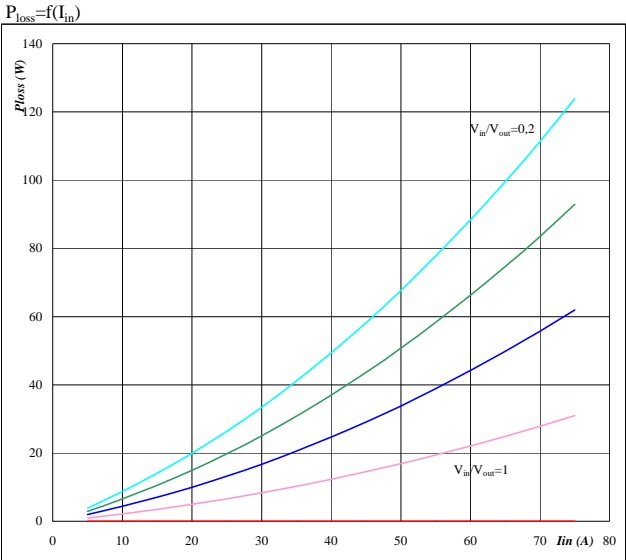
flowBoost0 **DC Boost Application** 600V/84A PS*

General conditions

BOOST	
V_{GEon}	= 15 V
V_{GEoff}	= 0 V
R_{gon}	= 4 Ω
R_{goff}	= 4 Ω

Figure 1. IGBT+MOSFET

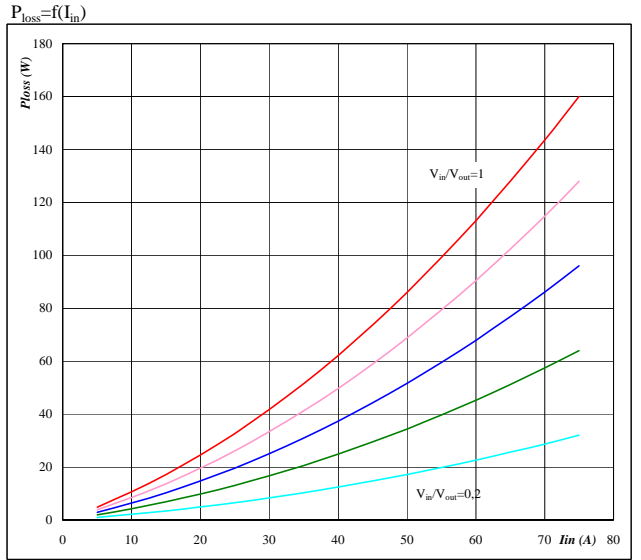
Typical average static loss as a function of input current I_{RMS}



Conditions: $T_j = 125$ °C
Ratio of input DC voltage to output DC voltage
parameter: V_{in}/V_{out} from 0,2 to 1,0
in 0,2 steps

Figure 2. FWD

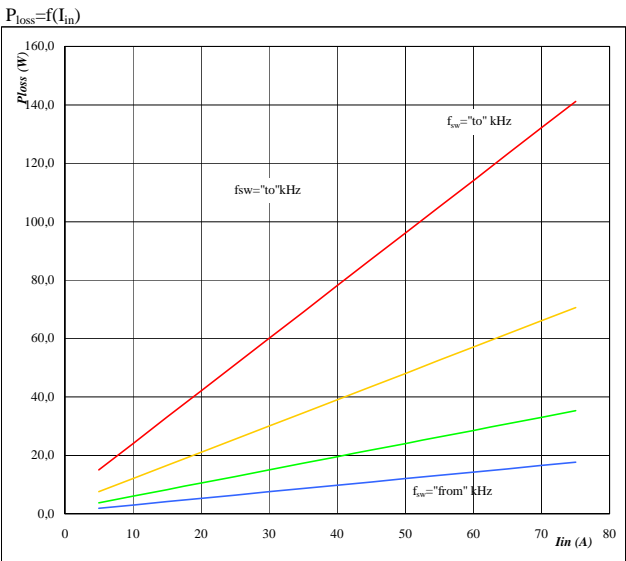
Typical average static loss as a function of input current I_{RMS}



Conditions: $T_j = 125$ °C
Ratio of input DC voltage to output DC voltage
parameter: V_{in}/V_{out} from 0,2 to 1,0
in 0,2 steps

Figure 3. IGBT+MOSFET

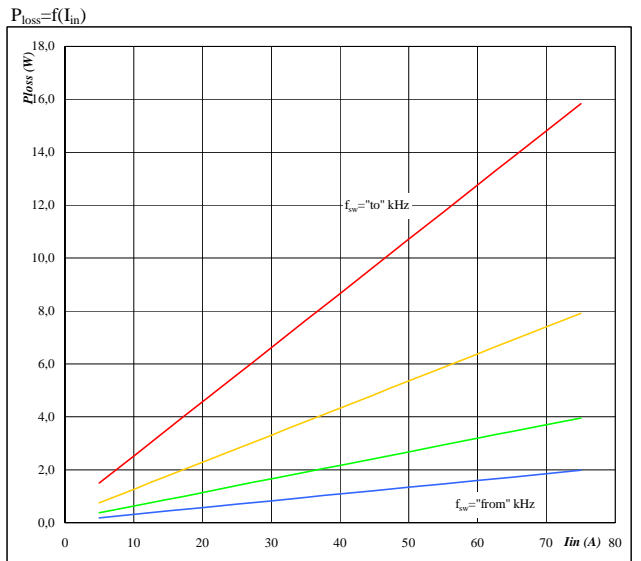
Typical average switching loss as a function of input current



Conditions: $T_j = 125$ °C
 $V_{out} = 350$ V
Sw. freq. f_{sw} from 16 kHz to 128 kHz
in steps of factor 2

Figure 4. FWD

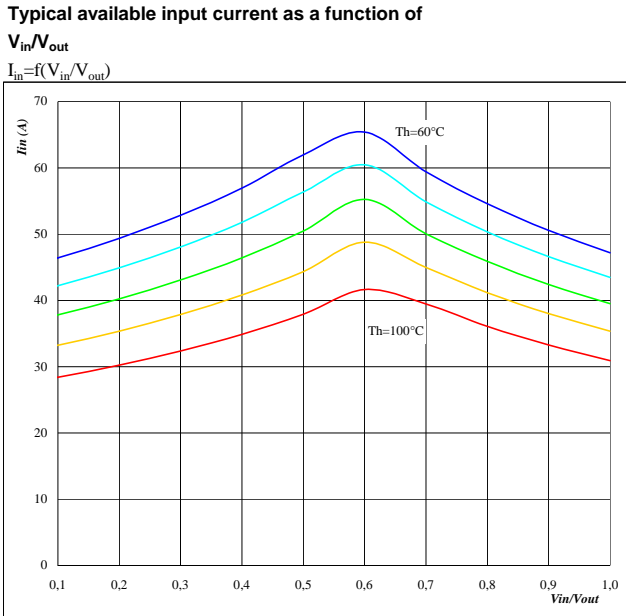
Typical average switching loss as a function of input current



Conditions: $T_j = 125$ °C
 $V_{out} = 350$ V
Sw. freq. f_{sw} from 16 kHz to 128 kHz
in steps of factor 2

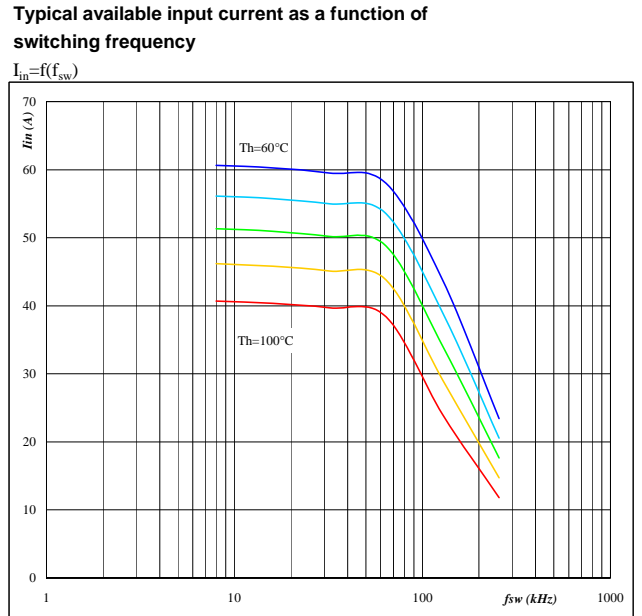
flowBoost0 DC Boost Application 600V/84A PS*

Figure 5. per PHASE



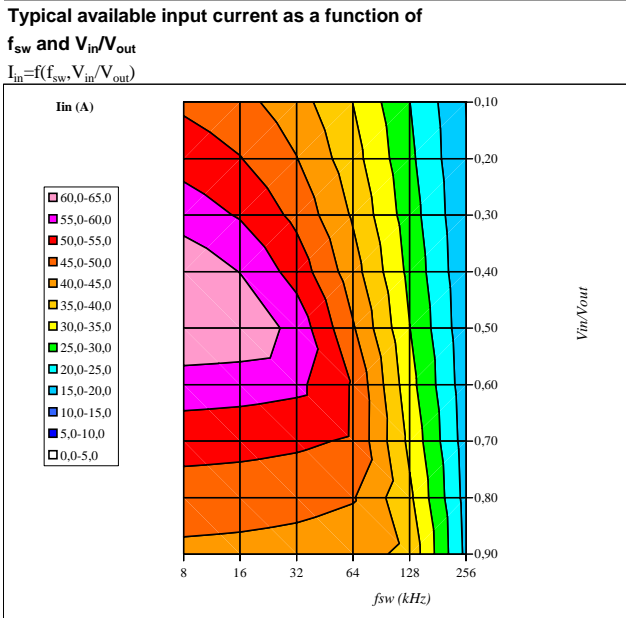
Conditions: $T_j = T_{jmax} - 25^\circ\text{C}$
 DC link= 350 V $f_{sw} = 50$ kHz
 parameter: Heatsink temp.
 Th from 60 °C to 100 °C
 in 10 °C steps

Figure 6. per PHASE



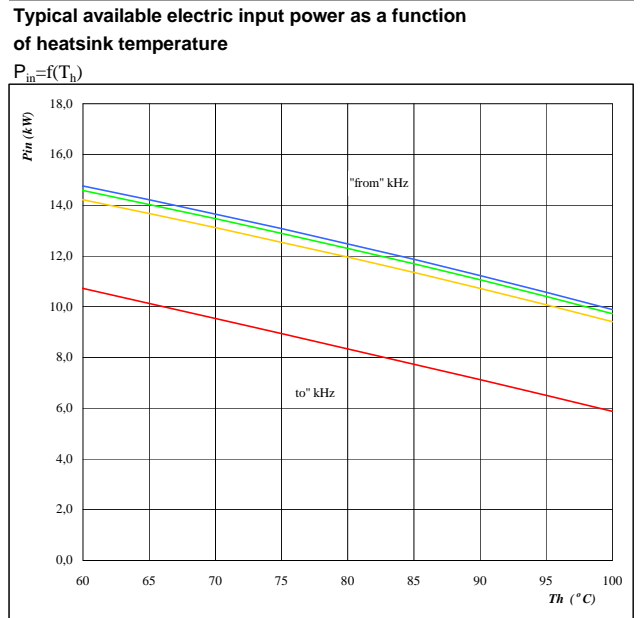
Conditions: $T_j = T_{jmax} - 25^\circ\text{C}$
 DC link= 350 V $V_{in} = 250$ V
 parameter: Heatsink temp.
 Th from 60 °C to 100 °C
 in 10 °C steps

Figure 7. per PHASE



Conditions: $T_j = T_{jmax} - 25^\circ\text{C}$
 DC link= 350 V
 Th= 80 °C

Figure 8. per PHASE

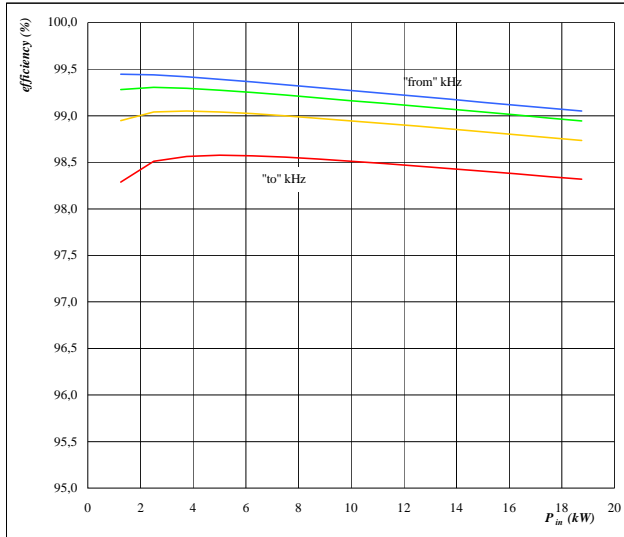


Conditions: $T_j = T_{jmax} - 25^\circ\text{C}$
 $V_{in} = 250$ V DC link= 350 V
 Sw. freq. f_{sw} from 16 kHz to 128 kHz

Figure 9. per PHASE

Typical efficiency as a function of input power

$$\eta = f(P_{in})$$



Conditions: $T_j = T_{jmax} - 25^\circ\text{C}$
 $V_{in} = 250\text{ V}$ DC link = 350 V
 parameter:
 Sw. freq. fsw from 16 kHz to 128 kHz